

# Power MOSFET

**TO-220AB**

**N-Channel MOSFET**

## PRODUCT SUMMARY

$V_{DS}$ (V)	200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.40
$Q_g$ max. (nC)	43	
$Q_{gs}$ (nC)	7.0	
$Q_{gd}$ (nC)	23	
Configuration	Single	

## FEATURES

- Dynamic  $dV/dt$  rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details



**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

## DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

## ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF630PbF
Lead (Pb)-free and halogen-free	IRF630PbF-BE3

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			$V_{DS}$	200	V
Gate-source voltage			$V_{GS}$	± 20	
Continuous drain current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	9.0	A
		$T_C = 100\text{ }^{\circ}\text{C}$		5.7	
Pulsed drain current <sup>a</sup>			$I_{DM}$	36	
Linear derating factor				0.59	W/°C
Single pulse avalanche energy <sup>b</sup>			$E_{AS}$	250	mJ
Repetitive avalanche current <sup>a</sup>			$I_{AR}$	9.0	A
Repetitive avalanche energy <sup>a</sup>			$E_{AR}$	7.4	mJ
Maximum power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		$P_D$	74	W
Peak diode recovery dV/dt <sup>c</sup>			dV/dt	5.0	V/ns
Operating junction and storage temperature range			$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s			300	
Mounting torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

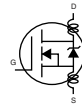

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 4.6\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 9.0\text{ A}$  (see fig. 12)
- $I_{SD} \leq 9.0\text{ A}$ ,  $dI/dt \leq 120\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^{\circ}\text{C}$
- 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

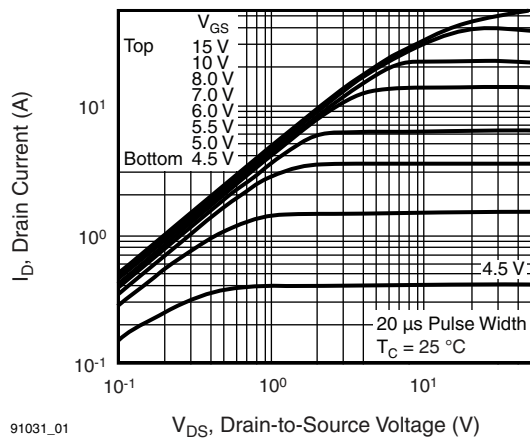
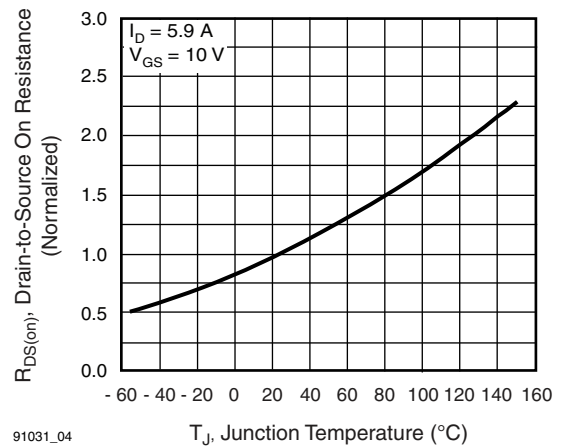
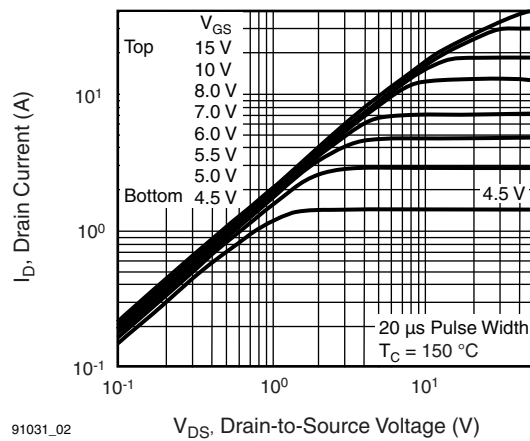
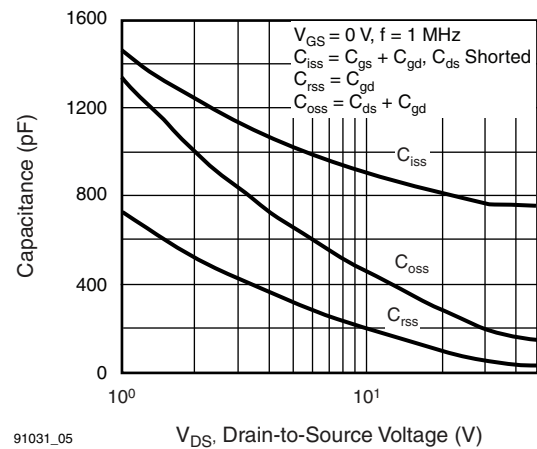
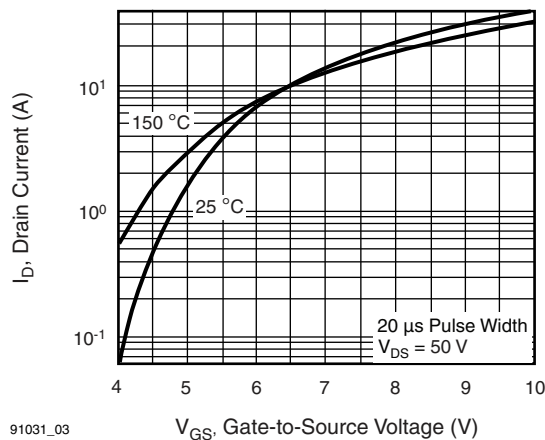
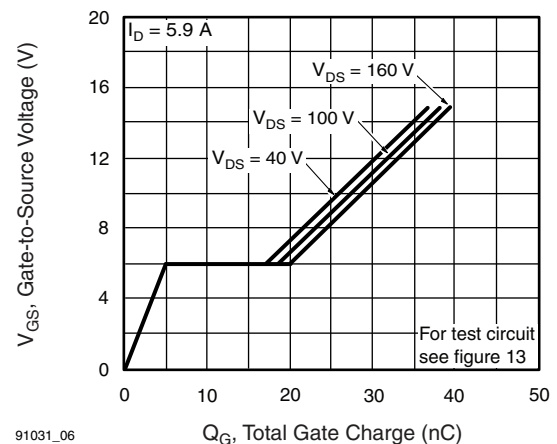
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJC}$	-	1.7	

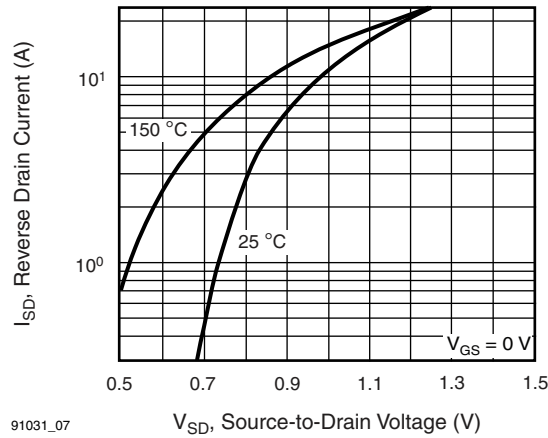
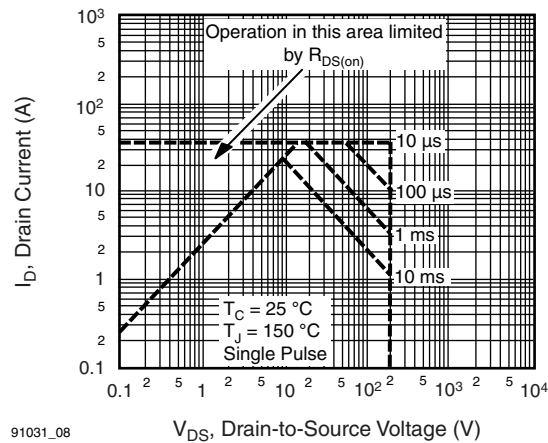
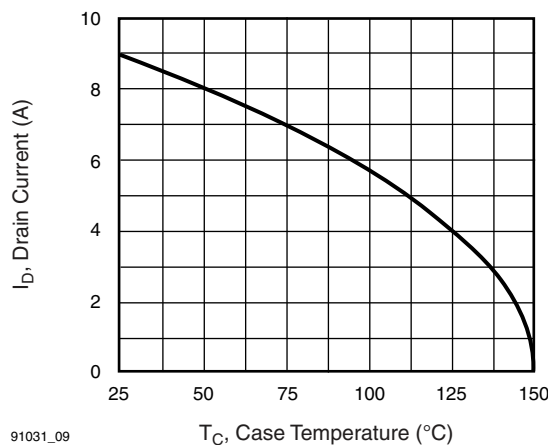
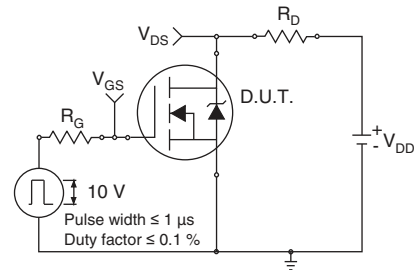
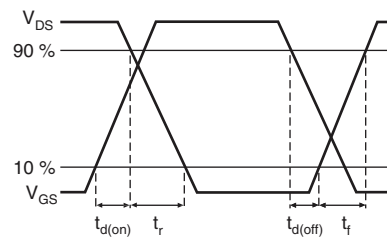
**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

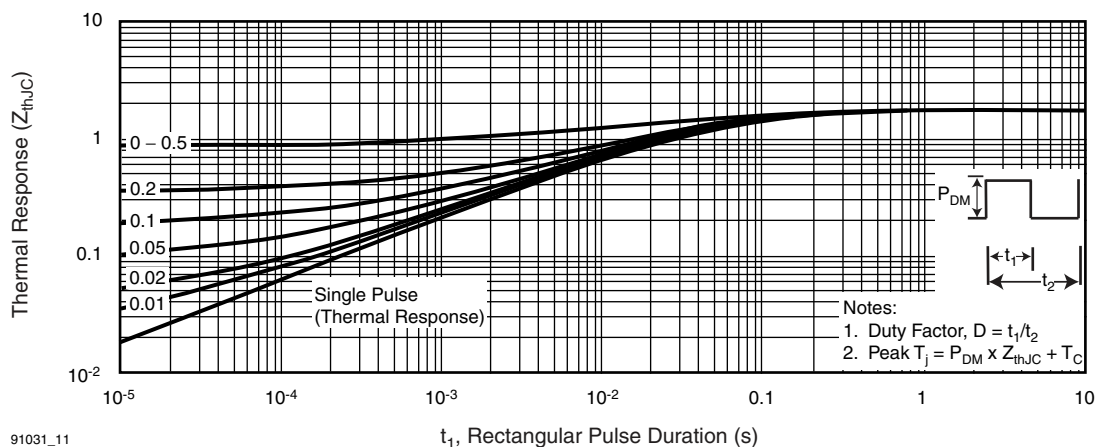
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		200	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.24	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V		-	-	25	μA
		V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	250	
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.4 A <sup>b</sup>	-	-	0.40	Ω
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 5.4 A		3.8	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5		-	800	-	pF
Output capacitance	C <sub>oss</sub>			-	240	-	
Reverse transfer capacitance	C <sub>rss</sub>			-	76	-	
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.9 A, V <sub>DS</sub> = 160 V, see fig. 6 and 13 <sup>b</sup>	-	-	43	nC
Gate-source charge	Q <sub>gs</sub>			-	-	7.0	
Gate-drain charge	Q <sub>gd</sub>			-	-	23	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 5.9 A, R <sub>g</sub> = 12 Ω, R <sub>D</sub> = 16 Ω, see fig. 10 <sup>b</sup>		-	9.4	-	ns
Rise time	t <sub>r</sub>			-	28	-	
Turn-off delay time	t <sub>d(off)</sub>			-	39	-	
Fall time	t <sub>f</sub>			-	20	-	
Gate input resistance	R <sub>g</sub>	f = 1 MHz, open drain		0.6	-	3.3	Ω
Internal drain inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal source inductance	L <sub>S</sub>			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	9.0	A
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>			-	-	36	
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 9.0 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	2.0	V
Body diode reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 5.9 A, dI/dt = 100 A/μs		-	170	340	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	1.1	2.2	nC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

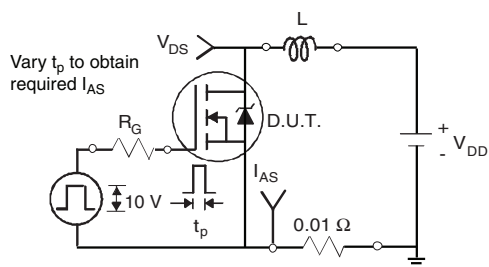
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$** 

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

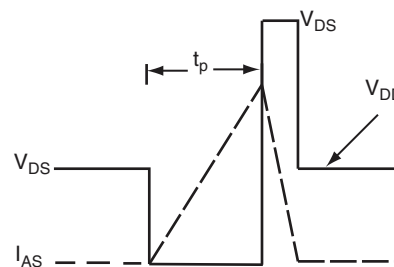

**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**



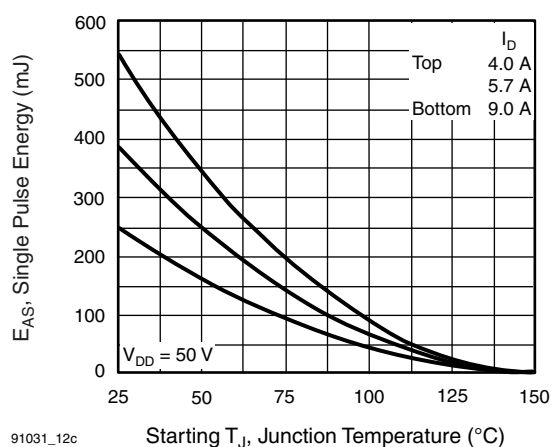
**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



**Fig. 12a - Unclamped Inductive Test Circuit**

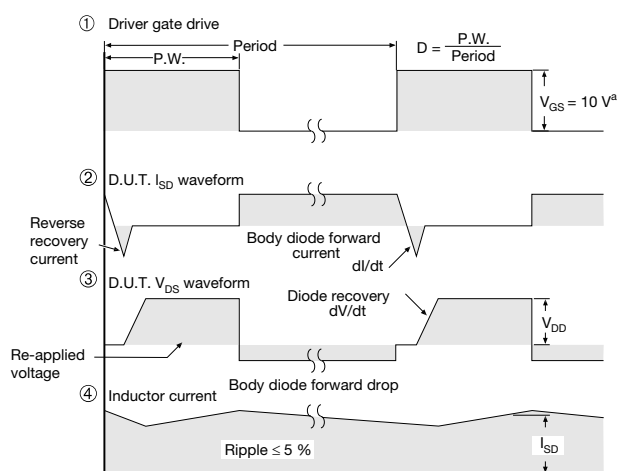
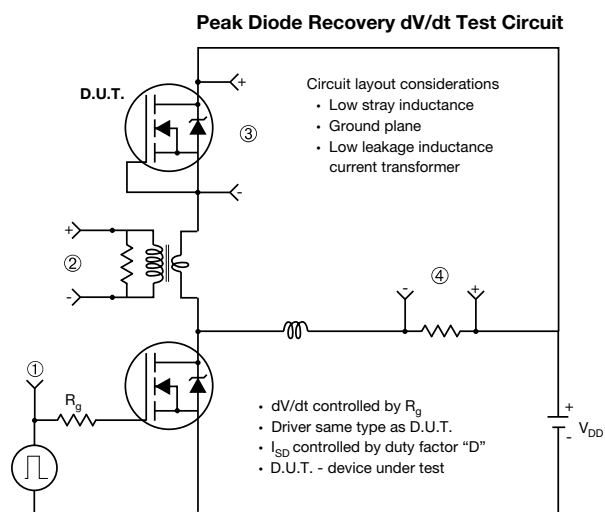


**Fig. 12b - Unclamped Inductive Waveforms**



**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**


**Fig. 13a - Basic Gate Charge Waveform**

**Fig. 13b - Gate Charge Test Circuit**


**Note**  
a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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## TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021  
DWG: 6031

### Note

- $M^*$  = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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